

This listing of claims will replace all prior versions, and listings of claims in the application:

LISTING OF CLAIMS:

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1. (Canceled)

2. (Currently Amended) A method of manufacturing a semiconductor device, comprising:

a first step of forming a semiconductor film over a substrate;

a second step of holding a catalytic element that promotes the crystallization of said semiconductor film in contact with an entire surface of said semiconductor film;

pl a third step of irradiating a laser beam shaped in a rectangle or a square while moving the laser beam from one side of said semiconductor film toward another side thereof to sequentially crystallize said semiconductor film to form a crystalline semiconductor film;

a fourth step of patterning said semiconductor film to form at least first and second semiconductor islands after the irradiation of the laser beam, and

a fifth step of forming a portion of a pixel matrix circuit comprising a at least first and second thin film transistors, transistor using said at least first and second semiconductor islands island, and forming a portion of a driving circuit comprising a second thin film transistor using said second semiconductor island,

~~wherein the pixel matrix circuit comprises said first thin film transistor and a driver circuit comprises said second thin film transistor, and~~

wherein said laser beam has an irradiation area of 10 cm<sup>2</sup> or more.

3. (Currently Amended) A method of manufacturing a semiconductor device, comprising:

a first step of forming a semiconductor film on a substrate having an insulating surface;

a second step of holding a catalytic element that promotes the crystallization of said semiconductor film in contact with an entire surface of said semiconductor film;

a third step of irradiating a laser beam shaped in a rectangle or a square from one side of said semiconductor film toward another side thereof while moving said substrate to sequentially crystallize said semiconductor film to form a crystalline semiconductor film,

a fourth step of patterning said semiconductor film to form at least first and second semiconductor islands after the irradiation of the laser beam, and

*End*  
a fifth step of forming a portion of a pixel matrix circuit comprising a at least first and second thin film transistors, transistor using said at least first and second semiconductor islands island, and forming a portion of a driving circuit comprising a second thin film transistor using said second semiconductor island,

~~wherein a pixel matrix circuit comprises said first thin film transistor and a driver circuit comprises said second thin film transistor, and~~

wherein said laser beam has an irradiation area of 10 cm<sup>2</sup> or more.

4. (Currently Amended; Withdrawn) A method of manufacturing a semiconductor device, comprising:

a first step of forming a semiconductor film over a substrate;

a second step of holding a catalytic element contained in a solution which promote the crystallization of said semiconductor film in contact with an entire surface of said semiconductor film;

a third step of irradiating a laser beam whose irradiation area in one shot is 10 cm<sup>2</sup> or more to said semiconductor film to crystallize said semiconductor film and to form a crystalline semiconductor film;

a fourth step of patterning said semiconductor film to form at least first and second semiconductor islands after the irradiation of the laser beam, and

a fifth step of forming a portion of a pixel matrix circuit comprising a at least first and second thin film transistors, transistor using said at least first and second semiconductor islands island, and forming a portion of a driving circuit comprising a second thin film transistor using said second semiconductor island;

~~wherein a pixel matrix circuit comprises said first thin film transistor and a driver circuit comprises said second thin film transistor.~~

5. (Currently Amended; Withdrawn) A method of manufacturing a semiconductor device, comprising:

a first step of forming a semiconductor film over a substrate;

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cont a second step of holding a compound containing a catalytic element which promotes the crystallization of said semiconductor film in contact with an entire surface of said semiconductor film;

a third step of irradiating a laser beam whose irradiation in one area in one shot is 10 cm<sup>2</sup> or more to said semiconductor film to crystallize said semiconductor film and to form a crystalline semiconductor film;

a fourth step of patterning said semiconductor film to form at least first and second semiconductor islands after the irradiation of the laser beam, and

a fifth step of forming a portion of a pixel matrix circuit comprising a at least first and second thin film transistors, transistor using said at least first and second semiconductor islands island, and forming a portion of a driving circuit comprising a second thin film transistor using said second semiconductor island;

~~wherein a pixel matrix circuit comprises said first thin film transistor and a driver circuit comprises said second thin film transistor.~~

6. (Currently Amended) A method of manufacturing a semiconductor device, comprising:

a first step of forming a semiconductor film over a substrate;

a second step of holding a catalytic element which promotes the crystallization of said semiconductor film in contact with an entire surface of said semiconductor film;

a third step of irradiating a laser beam whose irradiation area in one shot is 10 cm<sup>2</sup> or more to said semiconductor film to crystallize said semiconductor film and to form a crystalline semiconductor film;

a fourth step of conducting a thermal oxide processing in an oxide atmosphere to form an oxide film on the surface of said crystalline semiconductor film and gettering said catalytic element to said oxide film to remove or reduce said catalytic element existing in said crystalline semiconductor film;

a fifth step of patterning said semiconductor film to form at least first and second semiconductor islands after the irradiation of the laser beam, and

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a sixth step of forming a portion of a pixel matrix circuit comprising a at least first and second thin film transistors, transistor using said at least first and second semiconductor islands island, and forming a portion of a driving circuit comprising a second thin film transistor using said second semiconductor island;

~~wherein a pixel matrix circuit comprises said first thin film transistor and a driver circuit comprises said second thin film transistor.~~

7. (Previously Amended) A method of manufacturing a semiconductor device as claimed in claim 6, further comprising a step of removing said oxide film after said fourth step.

8. (Currently Amended) A method of manufacturing a semiconductor device, comprising:

a first step of forming a semiconductor film over a substrate;

a second step of holding a catalytic element which promotes the crystallization of said semiconductor film in contact with an entire surface of said semiconductor film;

a third step of irradiating a laser beam whose irradiation area in one shot is 10 cm<sup>2</sup> or more to said semiconductor film to crystallize said semiconductor film and to form a crystalline semiconductor film;

a fourth step of selectively adding phosphorus or boron to said crystalline semiconductor film and gettering said catalytic element to said added region by

conducting a heat treatment to remove or reduce said catalytic element existing in said crystalline semiconductor film;

a fifth step of patterning said semiconductor film to form at least first and second semiconductor islands after the irradiation of the laser beam, and

a sixth step of forming a portion of a pixel matrix circuit comprising a at least first and second thin film transistors, transistor using said at least first and second semiconductor islands island, and forming a portion of a driving circuit comprising a second thin film transistor using said second semiconductor island,

~~wherein a pixel matrix circuit comprises said first thin film transistor and a driver circuit comprises said second thin film transistor.~~

9. (Previously Amended) A method of manufacturing a semiconductor device as claimed in claim 1, 2, 3, 4, 5, 6 or 8, wherein a pulse width of the laser beam irradiated in the third step is 600 nsec to 1 msec.

10. (Previously Amended) A method of manufacturing a semiconductor device as claimed in claim 1, 2, 3, 4, 5, 6 or 8, wherein a laser energy density of the laser beam irradiated in the third step is 100 to 800 mJ/cm<sup>2</sup>.

11. (Original) A method of manufacturing a semiconductor device as claimed in claim 1, 2, 3, 4, 5, 6 or 8, wherein said catalytic element is at least one element selected from a group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Au, Ge, Pb and In.

12. (Original) A method of manufacturing a semiconductor device as claimed in claim 1, 2, 3, 4, 5, 6 or 8, wherein said semiconductor film comprises silicon.

13. (Original) A method of manufacturing a semiconductor device as claimed in claim 1, 2, 3, 4, 5, 6 or 8, wherein said crystalline semiconductor film has crystals of which crystal lattices are continuously coupled with each other.

14-19 (Canceled)

20. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising amorphous silicon on an insulating surface;

providing an entire surface of said semiconductor film with a crystallization promoting material comprising a metal;

crystallizing said semiconductor film by irradiating said semiconductor film with a pulsed laser beam,

patterning said semiconductor film to form at least first and second semiconductor islands after the irradiation of the laser beam, and

forming a portion of a pixel matrix circuit comprising a at least first and second thin film transistors, transistor using said at least first and second semiconductor islands island, and forming a portion of a driving circuit comprising a second thin film transistor using said second semiconductor island,

~~wherein a pixel matrix circuit comprises said first thin film transistor and a driver circuit comprises said second thin film transistor,~~

wherein said laser beam has a pulse width of 200 nsec or more, and

wherein said laser beam has an irradiation area of 10 cm<sup>2</sup> or more.

21. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film on an insulating surface;

providing an entire surface of said semiconductor film with a crystallization promoting material comprising a metal;

crystallizing said semiconductor film by irradiating said semiconductor film with a pulsed laser beam having a square shape cross section,

patterning said semiconductor film to form at least first and second semiconductor islands after the irradiation of the laser beam, and

forming a portion of a pixel matrix circuit comprising a at least first and second thin film transistors, transistor using said at least first and second semiconductor islands island, and forming a portion of a driving circuit comprising a second thin film transistor using said second semiconductor island,

~~wherein a pixel matrix circuit comprises said first thin film transistor and a driver circuit comprises said second thin film transistor, and~~

wherein said laser beam has a pulse width of 200 nsec or more, and an irradiation area of said laser beam is  $10 \text{ cm}^2$  or more.

22. (Previously Added) The method according to claim 20 or 21 wherein said metal is selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Au, Ge, Pb and In.

23. (Previously Added) The method according to claim 20 or 21 wherein an energy density of said laser beam at an irradiation area of said semiconductor film is 100 to  $800 \text{ mJ/cm}^2$ .

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